AMENDMENT TRANSMITTAL LETTER (Large Entity) Applicant(s): In-sung KIM et al.						Docket No. SEC.747	
Serial No. 09/640,754		Filing Date 3 August 2000	Hs	Examiner Hsien Ming LEE		Group Art Unit 2823	
Invention: SEM	THE SAME	EVICE PAVING SEL	F-ALIGNED	CONTACT A	AND MET	HOD OF	
		ent in the above-ident	ified applicati		NTS:		
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CLAIMS REMAIN		T	1	BER EXTRA	RATE	ADDITIONAL	
TOTAL CLAIMS	AFTER AMENDME		R CLAIM	S PRESENT 0	x \$18	FEE \$0.00	
INDEP. CLAIMS	3 -		=	0	x \$84		
Multiple Dependent Claims (check if applicable)						\$0.00	
TOTAL ADDITIONAL FEE FOR					ENDMENT	г \$0.00	
Please ch A duplica A check i The Com communi A duplica Any	te copy of this sheet additional filing feet patent application Signature PRINGER	ount No. et is enclosed. to cover the y authorized to charge y overpayment to Depe	e filing fee is e payment of osit Account C.F.R. 1.16.	the following No. 50-0	238	RECEIVED FEB 21 2003 tiated with TC 2800 MAIL ROOM	
VOLENTINE FF 12200 SUNRISE RESTON, VA 20 TEL. NO.: (703)	VALLEY DRIVE, 0191	SUITE 150		on first class ma Assistant Co 20231.	all under 37 (commissioner	ment and fee is being deposited with the U.S. Postal Service as C.F.R. 1.8 and is addressed to the for Patents, Washington, D.C. on Mailing Correspondence	

SEC.747



In re PATENT APPLICATION of:

In-sung KIM et al.

Group Art Unit: 2823

25 14 from

Serial No.: 09/640,754

Examiner: Hsien Ming LEE

MIGNEY

Filed: 18 August 2000

SEMICONDUCTOR DEVICE HAVING SELF-ALIGNED CONTACT AND METHOD OF FABRICATING THE SAME

AMENDMENT

RECEIVED
FEB 21 2003

Honorable Commissioner for Patents Washington, D.C. 20231

Sir:

In response to the Office Action dated 18 November 2002, please amend the above-identified patent application as follows:

IN THE CLAIMS:

Please substitute the following claims for the pending claims with the same claim numbers.

2. (Amended) A method of fabricating a semiconductor device, comprising:

forming a conductive region at the top of a semiconductor substrate;

forming a first interlayer dielectric layer on the semiconductor substrate over the entirety of the conductive region;